imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

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SEMICONDUC	TOR			TSM	6N50			
Pb-Free ROHS COMPLIANT		5	00V N-Channe	el Power M	OSFET			
ITO-220	TO-251	Pin Definition: 1. Gate	Key Parameter Performance					
(IPAK)	. ,	2. Drain 3. Source	Parameter	Value	Unit			
	69		V _{DS}	500	V			
			R _{DS(on)} (max)	1.4	Ω			
	2 ³		Q _g	26	nC			
TO-252 (DPAK)			C P					
			2500					
 Features Low R_{DS(ON)} 1.4Ω (N 	lax)	CT/	<u>Piccl</u>	k Diagram				
 Low gate charge typ 				р О				
Low Crss typical @	,							
Fast Switching	(47						
Ordering Informati	on O		G O	┘┋╾┥╶╹				
Part No.	Packa	Packing						
TSM6N50CI C0G		50pcs / Nabe		o s				
TSM6N50CP ROG		k _e	N Char	nel MOSFET				
TSM6N50CH C5G		75pcs / Tube	n-Char					
Note: "G" denotes fr no log	en- and Antimony-free .	those which contain						

Note: "G" denotes for hologen- and Antimony-free as those which contain <900ppm From ine, <900ppm chlorine (<15, 0ppm total Br + Cl) and <1000ppm antimony compounds

Absolute maximum Ratings T_A=25°C unless otherwise noted)

Paran sur	Symbol	Limit	Unit		
Prain-Cource Voltage	V _{DS}	500	V		
Cale-Source Voltage		V _{GS}	±30	V	
Continuous Drain Current	$T_A = 25^{\circ}C$		5.6	А	
	$T_A = 100^{\circ}C$	I _D	3	А	
Pulsed Drain Current (Note 1)	I _{DM}	15	А		
Single Pulse Avalanche Energy (Note 2)		E _{AS}	180	mJ	
Avalanche Current (Repetitive) (Note 3)		I _{AR}	5	А	
Total Downer Dissipation @ T 05°C	ITO-220	D	25	W	
Total Power Dissipation @ T _C = 25°C	TO-252. TO-251	P _{TOT}	90		
Operating Junction Temperature	TJ	150	°C		
Storage Temperature Range		T _{STG}	-55 to +150	°C	



Thermal Performance

Parameter (Note 4)			Symbol		Limit		Unit	
Thermal Resistance - Junction to Case ITO-220 TO-252. TO-251		ITO-220	-		5		°C/W	
		TO-252. TO-251	$R_{\Theta JC}$		2.78			
Thermal Resistance - Junction to Ambient			$R_{\Theta JA}$		62.5		°C/W	
Electrical Specifications (TJ=25	°C unle	ss otherwise noted)						
Parameter		Conditions	Symbo	N.n	Тур	Max	Unit	
Static								
Drain-Source Breakdown Voltage	V _{GS} =	$I_{D} = 250 \mu A$	BY LSS	500			V	
Drain-Source On-State Resistance	V _{GS} =	10V, I _D = 2.8A	DS(ON)		1.15	1.4	Ω	
Gate Threshold Voltage	V _{DS} =	V _{GS} , I _D = 250µA	V _{GS(TH)}	2.		4.0	V	
Zero Gate Voltage Drain Current	V _{DS} =	500V, $V_{GC} = 0V$	I _{DSS}	0		1	μA	
Gate Body Leakage	V _{GS} =	= ±20V, Vpe = 0V	I _{GSS}			±10	μA	
Forward Transfer Conductance	V _{DS} =	8V, h = 1A	Gits		2.6		S	
Dynamic ^(Note 5,6)			~~~~		•			
Total Gate Charge		2	Q _g		25	33		
Gate-Source Charge		400V, I _D = 5A, = 10V	Q _{gs}		5		nC	
Gate-Drain Charge	GS =		Q_gd		10			
Input Capacitance	t Capacitance		C _{iss}		680	900		
Output Capacitance		= 25V, V _{CS} = 0V, .000nz	C _{oss}		85	110	pF	
Reverse Transfer Capacitance			C _{rss}		15	20		
Switching ^(Note 5, 1)		1						
Turn-On Delay Tinle			t _{d(on)}		20	50		
Turn-On Hise Time	V _{GS} =	_S = 10V, I _D = 5A, _D = 250V, R _G =25Ω	t _r		40	90	ns	
Turr-O Delay Time	V _{DD} =		t _{d(off)}		90	190		
torn Ori Fall Time			t _f		45	100		
ource-Drain Diode Ratings and Cl	haracte	ristic						
Source Current	Integ	gral reverse diode in	I _S			5	Α	
Source Current (Pulse)	the M	IOSFET	I _{SM}			15	Α	
Diode Forward Voltage	I _S = 5	A, $V_{GS} = 0V$	V _{SD}			1.6	V	
Reverse Recovery Time	V _{GS} =	• 0V, I _S = 5A,	t _{fr}		430		ns	
Reverse Recovery Charge dl _F		I _F /dt = 100A/μs	Q _{fr}		2		μC	

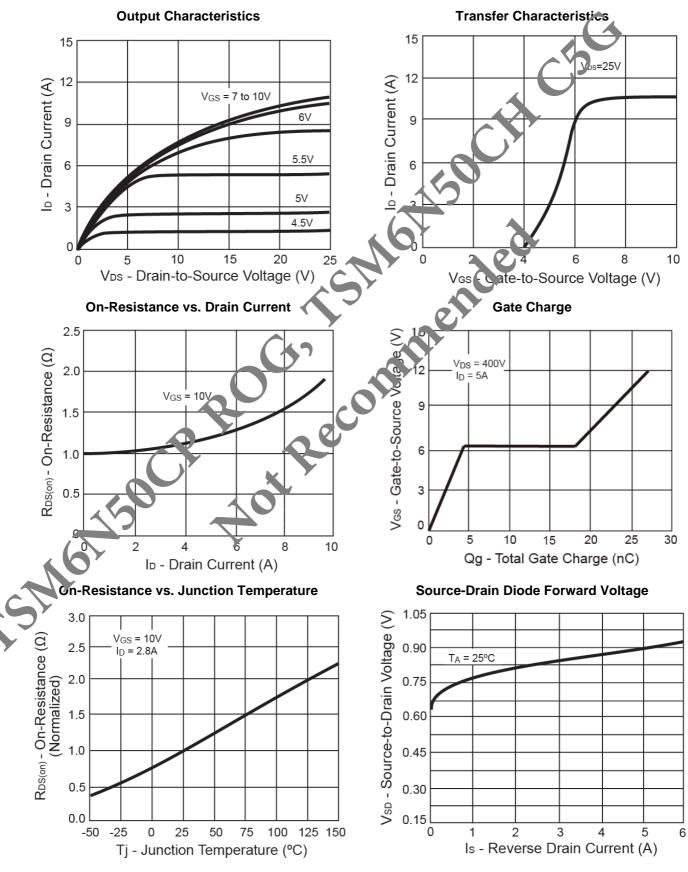
Note:

1. Limited by maximum junction temperature

- 2. $V_{DD} = 50V$, $I_{AS} = 5A$, L = 10mH, Starting $T_J = 25^{\circ}C$
- 3. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- 4. Surface mounted on FR4 board t \leq 10sec
- 5. Pulse test: pulse width \leq 300µS, duty cycle \leq 2%
- 6. Essentially Independent of Operating Temperature

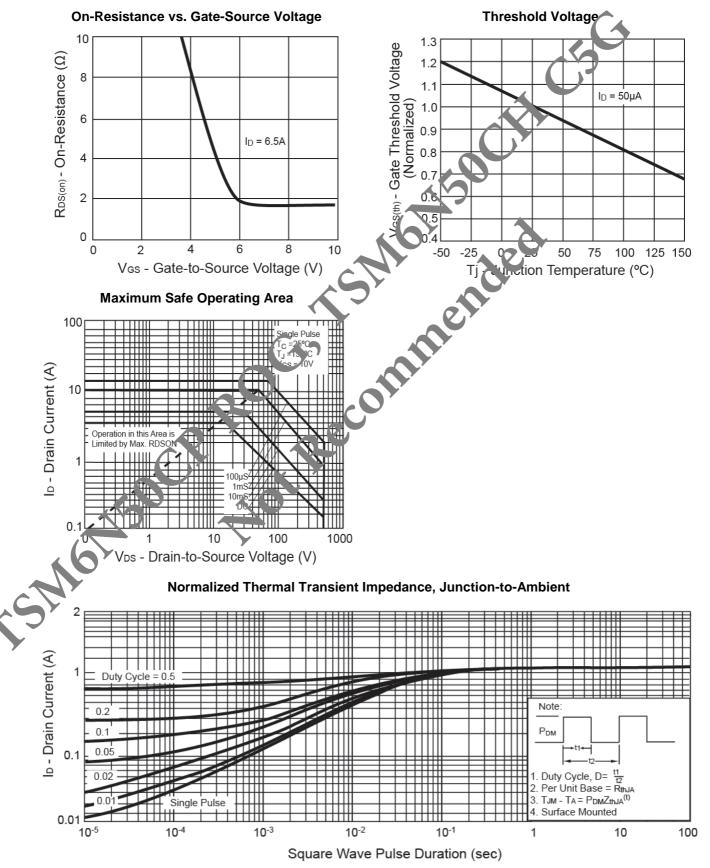


Electrical Characteristics Curves

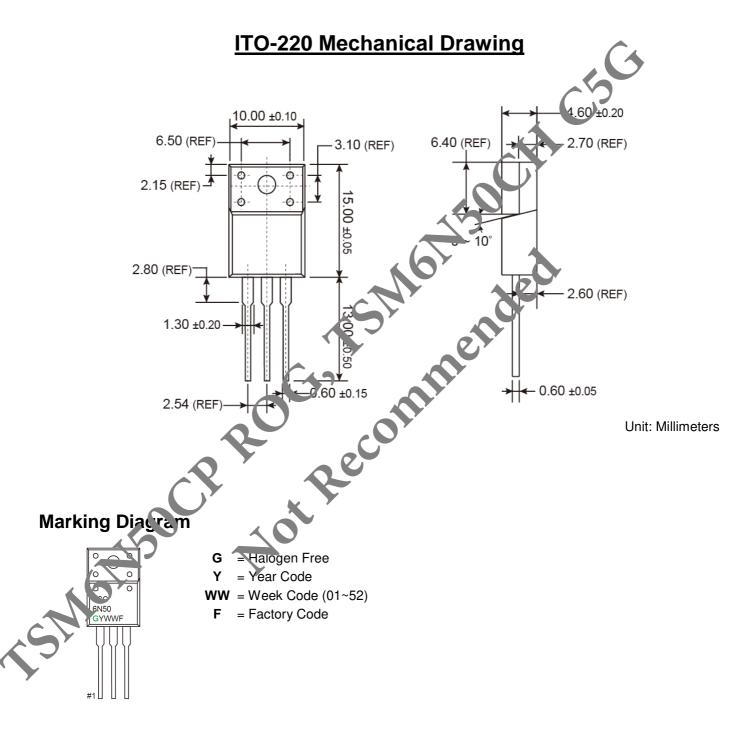




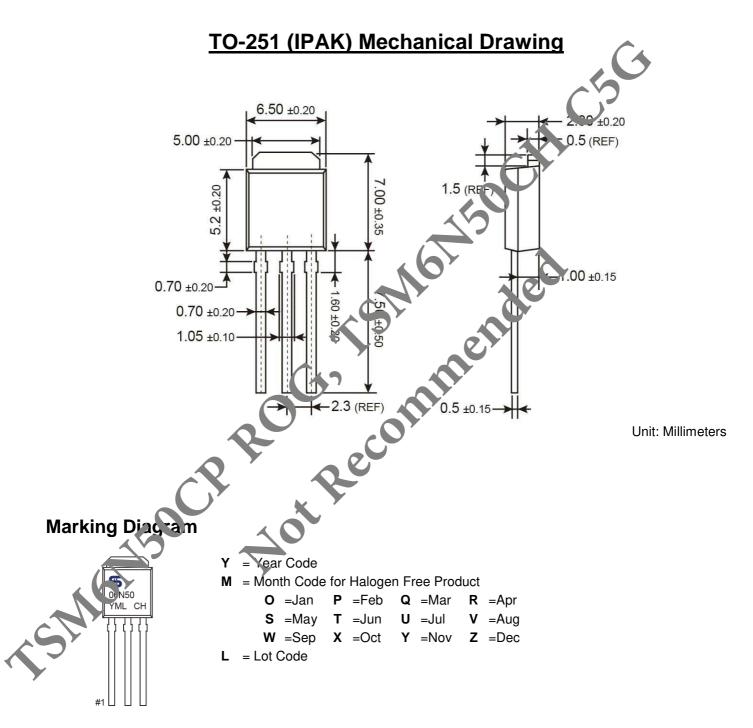
Electrical Characteristics Curves



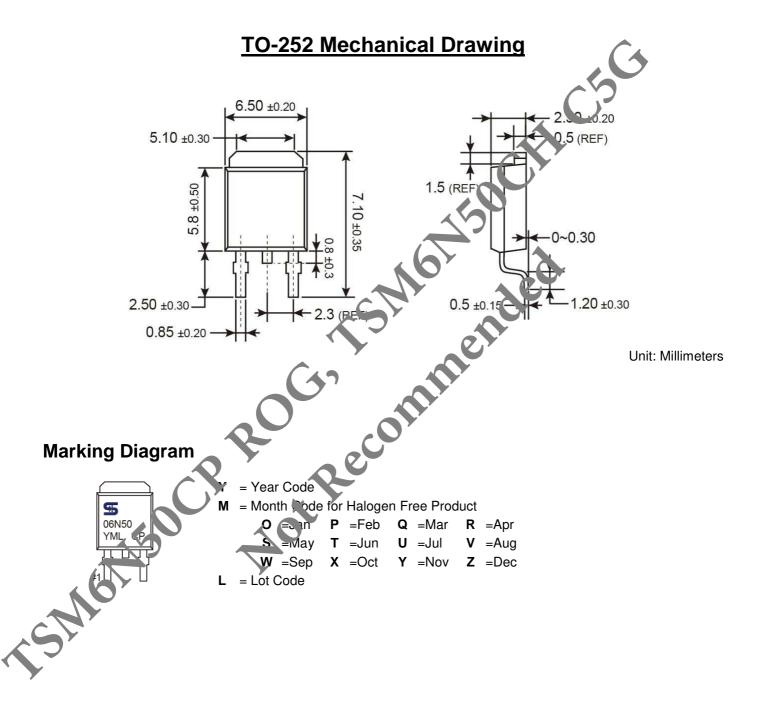














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